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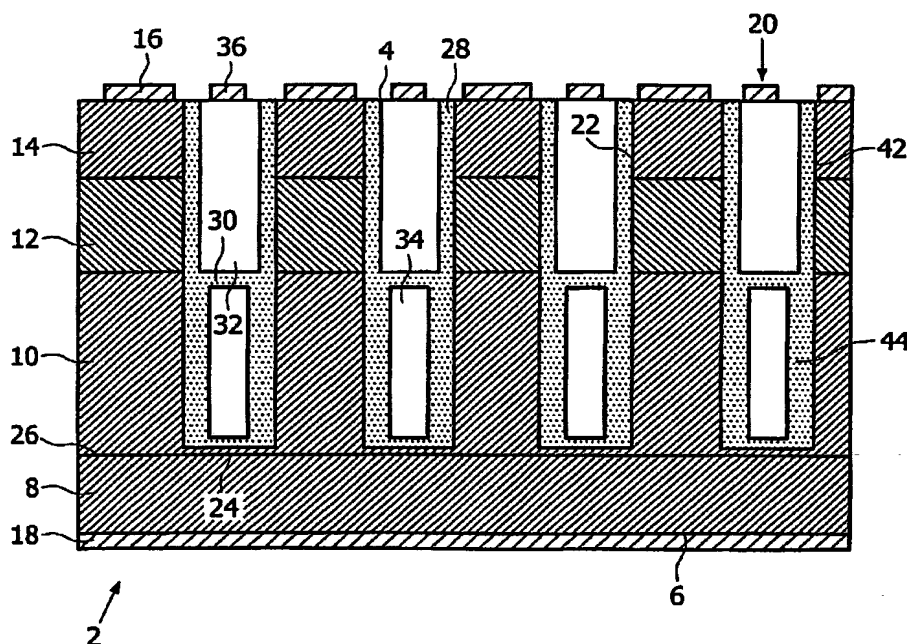
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(54) Title: TRENCH INSULATED GATE FIELD EFFECT TRANSISTOR



(57) Abstract: The invention relates to a trench MOSFET with drain (8), drift (10) body (12) and source (14) regions. The drift region is doped to have a high concentration gradient. A field plate electrode (34) is provided adjacent to the drift region (10) and a gate electrode (32) next to the body region (12).



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